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Temperature tunable LNA microchip lasers for helium pumping near 1083 nm

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Diode pumped microchip lasers offer many advantages : simplicity, compactness, the possibility to have a single frequency oscillation with a suitable reduction of the microcavity length, and finally if necessary to be tunable in the gain bandwidth [1, 2, 3].

We report the results obtained with different LNA microchip lasers which have been built and tested for helium magnetometry application.

A special crystal of LMA:Nd was pulled by the Czochralski method, in our laboratory, with a suitable composition in order to center a fluorescence peak near 1083 nm. From this crystal boule, different disks ($\phi = 5$ mm) were cut and polished in four thickness (170, 350, 600 and 1000 μ m). These LNA samples have received especially designed dichroïc mirrors in order to discriminate the 1083 nm emission against the strongest 1054 nm laser band.

Pumped with an 1 watt laser diode around 800 nm, laser emission at 1083 nm was observed with a power between 1 and 30 mw respectively for the LNA microchips having 170 and 1000 μ m thicknesses. The 170 μ m microchip laser oscillates with only two longitudinal modes.

Furthermore, the tunability of the laser wavelength at helium resonances (D0 and D1 D2) was easily obtained with a helium cell, by thermal regulation of the microchip lasers between 20 and 100°C.

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